AMENDMENTS TO THE CLAIMS

Please amend claims 1, 3, and 5; cancel claims 2 and 4 and add new claims 6-10 as follows:

1. (currently amended) A method for manufacturing a semiconductor device comprising ~~the steps of~~:

preparing a semiconductor substrate ~~defined as~~ with an active region and a field region;

forming ~~a number of~~ word lines in the active region and the field region of the semiconductor substrate;

depositing an insulator film ~~over the upper part of a structure to insulate word lines~~ on top of the word lines;

patterning the insulator film to open word lines ~~of~~ in the active region ~~whereby forming~~ to form a landing plug contact;

depositing a poly silicon film to fill ~~up~~ the landing plug contact;

performing a first polishing process using a slurry including ~~a first doping material~~ Boron and ~~flattening~~ planarizing the poly silicon film ~~only, whereby exposing~~ and the insulator film only; and

forming a landing plug by performing a second polishing process using a slurry including ~~a second doping material~~ phosphorous and by ~~flattening all the upper part of the structure~~ polishing the poly silicon film, the insulator film and the hard mask.

2. (canceled)

3. (currently amended) The method of claim ~~2~~ 1, wherein ~~the~~ a concentration of the Boron is in the range of 2wt% to 5wt%.

4. (canceled)

5. (currently amended) The method of claim 4 1, wherein ~~the~~ a concentration of the Phosphorus is in the range of 2wt% to 5wt%.

6. (new) A method for manufacturing a semiconductor device comprising:

preparing a semiconductor substrate having an active region and a field region;

forming word lines in the active region and the field region of the semiconductor substrate;

depositing an insulator film on top of the word lines;

patterning the insulator film to open word lines in the active region to form a landing plug contact;

depositing a poly silicon film to fill the landing plug contact and cover the insulator film;

performing a first polishing process using slurry including a first doping material to increase an etching rate of the poly silicon film with respect to the insulating film to flatten the poly silicon film only and expose the insulator film; and

forming a landing plug by performing a second polishing process using slurry including a second doping material to decrease the etching rate of the poly silicon film with respect to the insulating film and exposing the word lines.

7. (new) The method of claim 6, wherein the first doping material is boron.

8. (new) The method of claim 7, wherein a concentration of the boron is in the range of 2 wt % to 5 wt %.

9. (new) The method of claim 6, wherein the second doping material is phosphorus.

10. (new) The method of claim 9, wherein a concentration of the phosphorus is in the range of 2 wt % to 5 wt %.

11. (new) The method of claim 7, wherein the second doping material is phosphorus.

12. (new) The method of claim 8, wherein the second doping material is phosphorus.

13. (new) The method of claim 12, wherein a concentration of the phosphorus is in the range of 2 wt % to 5 wt %.